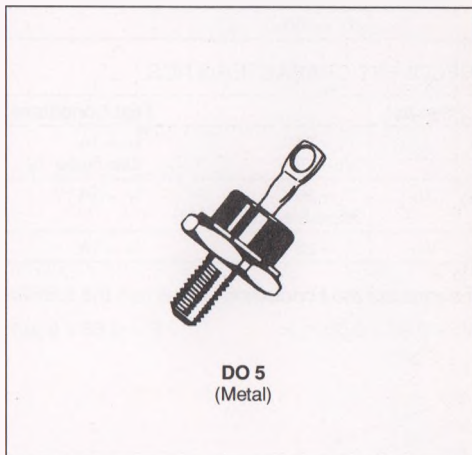


HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

- VERY LOW CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIMES
- HIGH SURGE CURRENT AND AVALANCHE CAPABILITY
- THE SPECIFICATIONS AND CURVES ENABLE THE DETERMINATION OF t_{rr} and I_{RM} AT 100°C UNDER USERS CONDITIONS
- EASE OF PARALLELING



DESCRIPTION

Low voltage drop rectifiers suited for switching mode power supply.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
I_{FRM}	Repetitive Peak Forward Current	$t_p \leq 20\mu s$	1000	A
$I_{F(RMS)}$	RMS Forward Current		100	A
$I_{F(AV)}$	Average Forward Current	$T_C = 85^\circ C$ $\delta = 0.5$	80	A
I_{FSM}	Surge non Repetitive Forward Current	$t_p = 10ms$ Sinusoidal	1500	A
P_{tot}	Power Dissipation	$T_C = 90^\circ C$	80	W
T_{stg} T_j	Storage and Junction Temperature Range		- 40 to 150	°C

Symbol	Parameter	BYW 08-				Unit
		50	100	150	200	
V_{RRM}	Repetitive Peak Reverse Voltage	50	100	150	200	V
V_{RSM}	Non Repetitive Peak Reverse Voltage	55	110	165	220	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction-case	0.75	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R	T _j = 25°C	V _R = V _{RRM}			50	μA
	T _j = 100°C				5	mA
V _F	T _j = 25°C	I _F = 80A			1.05	V
	T _j = 100°C				0.92	

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
t _{rr}	T _j = 25°C V _R = 30V	I _F = 1A di _F /dt = - 50A/μs see figure 12			60	ns
t _{fr}	T _j = 25°C Measured at 1.1 x V _F	I _F = 1A t _r = 5ns		10		ns
V _{FP}	T _j = 25°C	I _F = 1A t _r = 5ns		1.5		V

To evaluate the conduction losses use the following equations :

$$V_F = 0.66 + 0.0021 I_F \qquad P = 0.66 \times I_{F(AV)} + 0.0021 I_{F(RMS)}^2$$

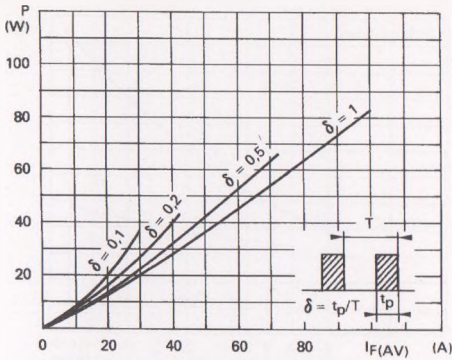


FIGURE 1 : Power losses versus average current

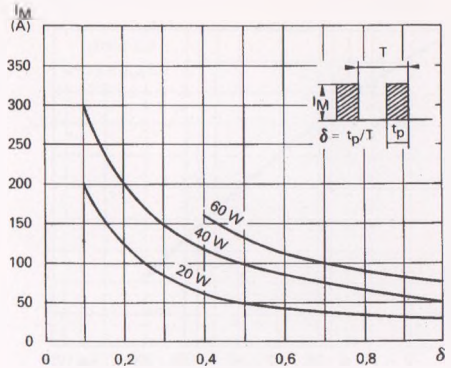


FIGURE 2 : Peak current versus form factor

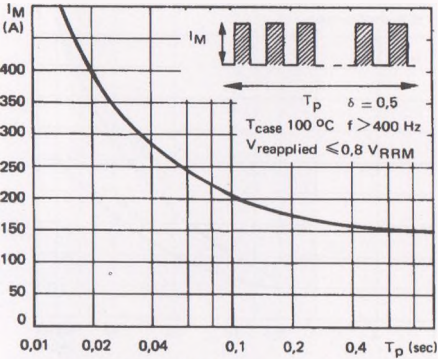


FIGURE 3 : Non repetitive peak surge current versus duration

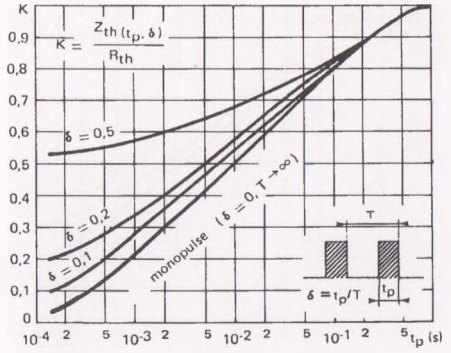


FIGURE 4 : Thermal impedance versus pulse width

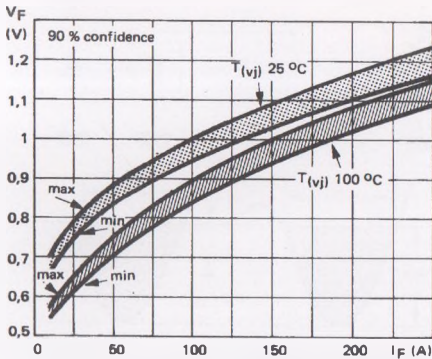


FIGURE 5 : Voltage drop and spread versus forward current

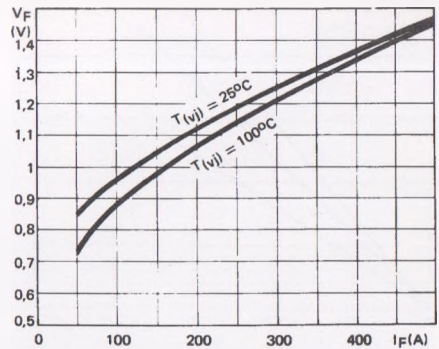


FIGURE 6 : Voltage drop versus forward current

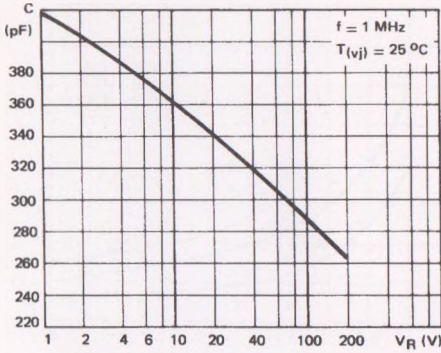


FIGURE 7 : Capacitance versus reverse voltage applied

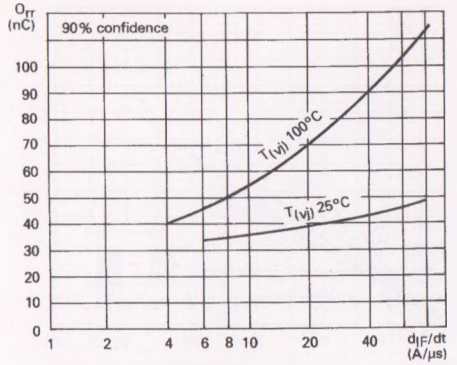


FIGURE 8 : Recovery charge versus diF/dt

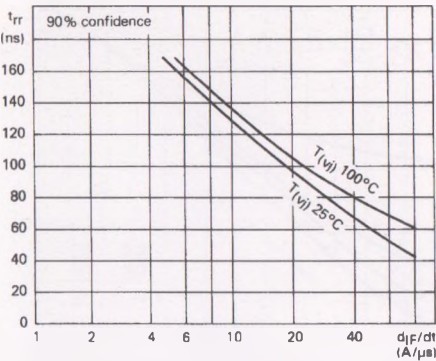


FIGURE 9 : Recovery time versus diF/dt

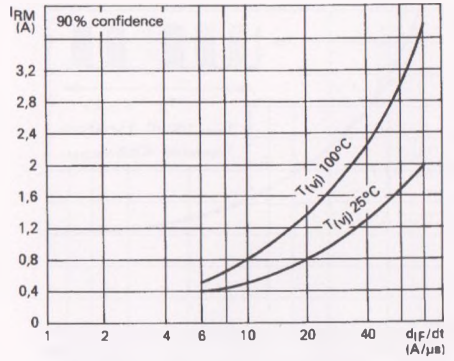


FIGURE 10 : Peak reverse current versus diF/dt

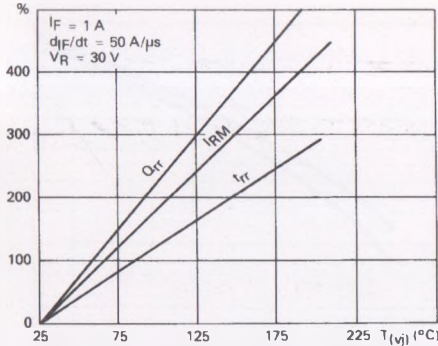


FIGURE 11 : Dynamic parameters versus junction temperature

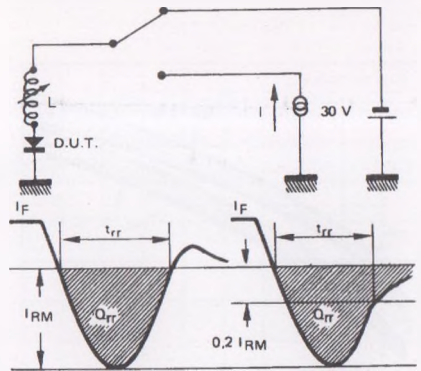


FIGURE 12 : Measurement of t_{rr} (fig. 9) and I_{RM} (fig. 10)